

Abstract of the Disclosure

A field oxide film for element isolation is formed on an SOI substrate having a silicon layer formed on an insulating layer, an active nitride film is wet-etched to reduce its film thickness to a value small enough to allow the edge of the silicon layer to become exposed and ions of a channel stopping impurity are implanted only into the edge of the silicon layer through self-alignment either vertically or at an angle by using the active nitride film as a mask. Through this manufacturing method, a field effect transistor which achieves a small gate length, is free from the adverse effect of a parasitic transistor and thus does not readily manifest a hump, and allows a reduction in the distance between an nMOS and a pMOS provided next to each other is realized.